

<b>Notice of References Cited</b>			Application/Control No. 10/595,640	Applicant(s)/Patent Under Reexamination TSUBATA ET AL.	
			Examiner Earl N. Taylor	Art Unit 2818	Page 1 of 1

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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